

Substitute for form 1449 A &amp; B/PTO

Complete if Known

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Application Number	09/924,872
Confirmation Number	3695
Filing Date	August 9, 2001
First Named Inventor	Hiroynki NAGASAWA
Art Unit	2812
Examiner Name	UNKNOWN
Attorney Docket Number	Q65781

Sheet 1 of 1

**U.S. PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code <sup>2</sup> (if known)		
		US			
		US			
		US			
		US			
		US			
		US			
		US			
		US			
		US			

**FOREIGN PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation <sup>6</sup>
		Country Code <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)			
SM		EP	0322615	A1	7/5/89	Takashi ESHITA et al.	Yes
SM		EP	09052798		2/25/97	Yoichi YAMAGUCHI	English Abstract

**OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation <sup>6</sup>
SM		R.S. Kem et al.; "Deposition and Doping of Silicon Carbide By Gas-Source Molecular Beam Epitaxy"; Appl. Phys. Lett. 71 (10); September 8, 1997; pp. 1356-1358.	
		Jin-Hyo Boo et al.; "Low-Temperature Epitaxial Growth of Cubic SiC Thin Films On Si(111) Using Supersonic Molecular Jet of Single Source Precursors"; Thin Solid Films 343-344 (1999); pp. 650-655.	
		Tatsuo YOSHINOBU et al.; "Atomic Level Control In Gas Source MBE Growth of Cubic SiC"; Journal of Crystal Growth; Nos. 1-4; Part I; January 1990; pp. 520-524.	
		Tsunenobu Kimoto et al.; "Incorporation Mechanism of N, Al, and B Impurities in Chemical Vapor Deposition of SiC"; Applied Physics Letters; No. 16; October 16, 1995; pp. 2385-2387.	
		J.J. Sumakeris et al.; "Layer-By-Layer Growth of SiC at Low Temperatures"; Thin Solid Films; No. 1-2; March 25, 1993; pp. 219-224.	
SM		V. Cimalla et al.; "Growth of Thin $\beta$ -SiC Layers by Carbonization of Si Surfaces by Rapid Thermal Processing"; Materials Science & Engineering B Solid-State Materials for Advanced Technology; Nos. 1-3; January 1995; pp. 170-175.	

Examiner Signature

Date Considered

\*EXAMINER Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of Office that issued the document, by the two-letter code (WIPO Standard ST 3). For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST 16 if possible. Applicant is to indicate here if English language Translation is attached.

<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov), MPEP 901.04 or in the comment box of this document. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST 3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST 16 if possible. <sup>6</sup> Applicant is to indicate here if English language Translation is attached.